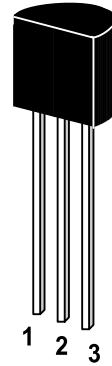


ST 2SA562

PNP Silicon Epitaxial Planar Transistor
for switching and AF amplifier applications.

The transistor is subdivided into two group, O and Y according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.

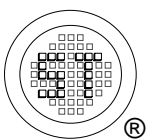


1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings (Ta=25°C)

	Symbol	Value	Unit
Collector Base Voltage	$-V_{CB0}$	35	V
Collector Emitter Voltage	$-V_{CE0}$	30	V
Emitter Base Voltage	$-V_{EB0}$	5	V
Collector Current	$-I_C$	500	mA
Base Current	$-I_B$	100	mA
Power Dissipation	P_{tot}	500	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_s	-55 to +150	°C



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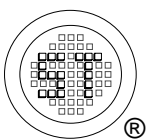


Dated : 07/12/2002

ST 2SA562

Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE}=1\text{V}$, $-I_C=100\text{mA}$ Current Gain Group O Y	h_{FE}	70	-	140	-
	h_{FE}	120	-	240	-
	h_{FE}	25	-	-	-
at $-V_{CE}=6\text{V}$, $-I_C=400\text{mA}$					
Collector Cutoff Current at $-V_{CB}=35\text{V}$	$-I_{CBO}$	-	-	0.1	μA
Emitter Cutoff Current at $-V_{EB}=5\text{V}$	$-I_{EBO}$	-	-	0.1	μA
Collector Emitter Saturation Voltage at $-I_C=100\text{mA}$, $-I_B=10\text{mA}$	$-V_{CE(sat)}$	-	0.1	0.25	V
Base Emitter Voltage at $-I_C=100\text{mA}$, $-V_{CE}=1\text{V}$	$-V_{BE}$	-	0.8	1.0	V
Transition Frequency at $-V_{CE}=6\text{V}$, $-I_C=20\text{mA}$	f_T	-	200	-	MHz
Collector Output Capacitance at $-V_{CB}=6\text{V}$, $f=1\text{MHz}$	C_{OB}	-	13	-	pF



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ISO/TS 16949 : 2002 Certificate No. 05103
 ISO 14001:2004 Certificate No. 7116
 ISO 9001:2000 Certificate No. 0508098

Dated : 07/12/2002